

IN THE SPECIFICATION

*6*  
Please delete the paragraphs beginning a page 6, line 15 and ending at page 8, line 13  
in their entirety, and substitute therefore the following:

-- A semiconductor device according to an aspect of the present invention includes:  
a drain layer having a first conductivity type;  
a drift layer having the first conductivity type, which is formed on the drain layer and  
has an impurity concentration lower than that in the drain layer;  
a RESURF layer having a second conductivity type and formed to extend from a  
surface of the drift layer into the drain layer, the RESURF layer forming a superjunction  
structure together with the drift layer and forming a depletion layer in the drift layer; and  
one of a first insulating film and first semiconductor layer formed to extend from a  
surface of the RESURF layer to the drain layer, the first semiconductor layer having an  
impurity concentration lower than those in the drift layer and RESURF layer, the RESURF  
layer being located between the drain layer and one of the first insulating film and first  
semiconductor layer and between the drift layer and one of the first insulating film and first  
semiconductor layer.--

Docket No. 244748US2SDIV  
Inventor: Wataru SAITO ET AL  
Preliminary Amendment Filed: November 18, 2003

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Please amend the paragraph at page 1, lines 4-10 to read as follows:

This application is based upon and claims the benefit of priority under 35 USC §119  
from the prior Japanese Patent Applications No. 2001-175041, filed June 11, 2001; No. 2001-  
276801, filed September 12, 2001; No. 2001-298311, filed September 27, 2001, and under 35  
USC §120 from U.S. Serial No. 10/163,651, filed June 7, 2002, the entire contents of all of  
*Now U.S. Patent No. 6,693,338*  
which are incorporated herein by reference.

*QW*  
Please delete the existing paragraph at page 6, line 15 to page 7, line 15 and insert the  
following new paragraph:

A semiconductor device according to an aspect of the present invention comprising:  
a drain layer having a first conductivity type;  
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a RESURF layer having a second conductivity type and formed to extend from a  
surface of the drift layer into the drain layer, the RESURF layer forming a superjunction  
structure together with the drift layer and forming a depletion layer in the drift layer.

Please delete the paragraph at page 7, line 16 to page 8, line 13 in its entirety.

Please delete page 34, lines 2-15, in their entirety and substitute therefore the  
following new Abstract of the Disclosure on the page attached hereto.

10/714916

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